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Dear Editor,

We hereby submit the paper entitled "Statistical learning for engineering data: An application with 1/f noise measurements from on-wafer MOSFETs", co-authored by Gámiz, M.L., Kalén, A., Nozal-Cañadas, R., and Raya-Miranda, R.

The general motivation of this paper is to ascertain possible correlations between the characteristic threshold voltage and the noise power level of the transistors on a wafer based on a sample of noise measurements at various levels of frequency. The experiment providing the data has been performed in the Laboratory of Nanoelectronics in the Research Centre for Information and Communications Technologies (CITIC-UGR) at the University of Granada (Spain). To analyze the data classical and most broadly used statistical methods are not appropriate for this practical application because the basic assumptions where they lie on are not met. More sophisticated methods are required. To solve the problem we have designed a strategy based on the most novel nonparametric techniques which are free of questionable parametric assumptions. The data have been processed by developing original scripts in the programming environment R.

We believe that the insights developed in this paper can eventually help to improve the production process and further the reliability of MOSFET transistors.
We hope that our paper can meet the high standards of *IEEE Transactions on Knowledge and Data Engineering.*

Yours sincerely,

M.L. Gámiz